ELECTRONICS, INC.
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NTE2661
Silicon NPN Transistor
Horizontal Deflection Output for HDTV

Features:
- High Speed: t_f = 0.15μs Typ
- High Breakdown Voltage: V_{CBO} = 1700V
- Low Saturation Voltage: $V_{CE(sat)}$ = 3V Max

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–to–Base Voltage, V_{CBO} 1700V
Collector–to–Emitter Voltage, V_{CEO} 600V
Emitter–to–Base Voltage, V_{EBO} 5V
Collector Current, I_C
  Continuous 20A
  Peak 40A
Base Current, I_B 10A
Collector Power Dissipation (T_C = +25°C), P_C 200W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

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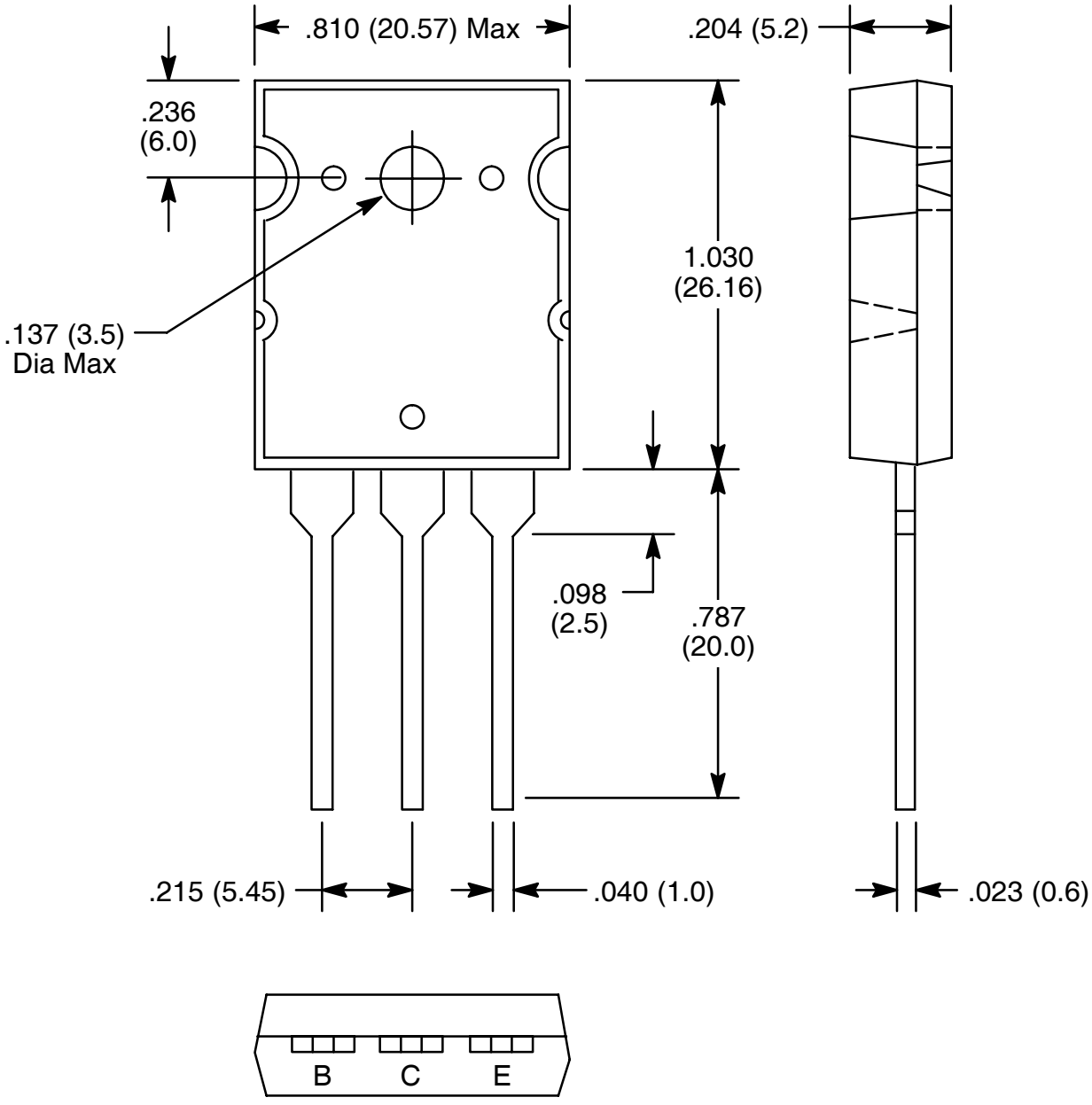
Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 1700V, I_E = 0	–	–	1.0	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	10	μA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	600	–	–	V
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 2A	10	–	30	–
		V_{CE} = 5V, I_C = 11A	4.5	–	8.5	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 11A, I_B = 2.75A	–	–	3	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 11A, I_B = 2.75A	–	1.0	1.3	V
Transition Frequency	f_T	V_{CE} = 10V, I_E = 0.1A	–	1.7	–	MHz
Collector Output capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	290	–	pF
Storage Time	t_{stg}	I_C(peak) = 10A, I_{B1} = 1.8A, f_H = 64kHz	–	2.5	4.0	μs
Fall Time	t_f		–	0.15	0.3	μs



NOTE: Pin2 connected to heatsink